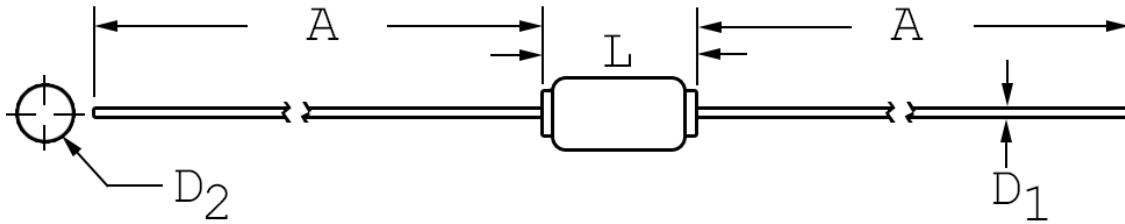


Diodes > High-Speed/Fast Recovery



	A	L	D ₁	D ₂
mm	25.4	3.94	0.78 DIA.	2.16 DIA.
inches	1.0 MIN.	0.155 MAX.	0.030±0.002	0.085 MAX.

FEATURES

- Hermetically Sealed Voidless-Glass
- High Reliability
- Excellent operating temp range
- Triple-layer passivation
- High voltage with ultra-fast recovery time

SPECIFICATIONS

	Value	Unit
Military Grade	N	---
I _O Max. Output Current	1.2	A
V _{RRM} Repeat Peak Rev. V	600	V
T _{RR} Max. Rev. Rec. Time	30	nS
@ I _F Test Condition	500	mA
@ I _R Test Condition	1.0	A
V _{FM} Max. Forward Voltage	1.4	V
I _{RM} Max. Reverse Current	500	nA
@ V _R Test Condition	600	V
I _{RM} Max. Peak Rev. Current	200	µA
@ Temp. Test Condition	150	°C
Semiconductor Material	Silicon	---
Maximum Operating Temp.	175	°C
Package Style	Axial-4	---
Mounting Style	T	---

While this rectifier is consumer-rated, it is ideal for high reliability applications specifically in designs with high temperature tolerance requirements. The 1N6622 features very low switching loss at high temperatures, is metallurgically bonded, and is encased in a non-cavity (voidless) glass package.

